



SDI FINAL EVALUATION FORM 1.1

PART 1:

Journal Name:	Physical Science International Journal
Manuscript Number:	2015_PSIJ_17567
Title of the Manuscript:	Modeling and Simulation of High Blocking Voltage in 4H Silicon Carbide Bipolar Junction Transistors
Type of Article	

PART 2:

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
Please revise Figure 2, Figure 3, Figure 4, Figure 5, Figure 6, Figure 7 using Origin. Figures will be better after revision.	Figures 2 through Figure 7 are revised and redone!